

thinQ!™ SiC Schottky Diode

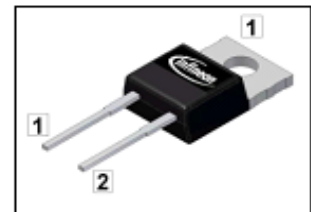
Features

- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery / No forward recovery
- Temperature independent switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target applications
- Optimized for high temperature operation
- Lowest Figure of Merit Q_C/I_F

Product Summary

V_{DC}	1200	V
Q_C	27	nC
$I_F; T_C < 130\text{ °C}$	7.5	A

PG-TO220-2



thinQ!™ Diode designed for fast switching applications like:

- SMPS e.g.; CCM PFC
- Motor Drives; Solar Applications; UPS

Type	Package	Marking	Pin 1	Pin 2
IDH08S120	PG-TO220-2	D08S120	C	A

Maximum ratings

Parameter	Symbol	Conditions	Value	Unit
Continuous forward current	I_F	$T_C < 130\text{ °C}$	7.5	A
Surge non-repetitive forward current, sine halfwave	$I_{F,SM}$	$T_C = 25\text{ °C}, t_p = 10\text{ ms}$	39	
		$T_C = 150\text{ °C}, t_p = 10\text{ ms}$	33	
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25\text{ °C}, t_p = 10\text{ μs}$	160	
i^2t value	$\int i^2 dt$	$T_C = 25\text{ °C}, t_p = 10\text{ ms}$	7	A^2s
		$T_C = 150\text{ °C}, t_p = 10\text{ ms}$	5	
Repetitive peak reverse voltage	V_{RRM}	$T_J = 25\text{ °C}$	1200	V
Diode dv/dt ruggedness	dv/dt	$V_R = 0 \dots 960\text{ V}$	50	V/ns
Power dissipation	P_{tot}	$T_C = 25\text{ °C}$	100	W
Operating and storage temperature	T_J, T_{stg}		-55 ... 175	$^{\circ}C$
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	1.6mm (0.063 in.) from case for 10s	260	
Mounting torque		M3 and M3.5 screws	60	Mcm

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	1,5	K/W
Thermal resistance, junction - ambient	R_{thJA}	Thermal resistance, junction- ambient, leaded	-	-	62	

Electrical characteristics, at $T_j=25\text{ }^{\circ}\text{C}$, unless otherwise specified

Static characteristics

DC blocking voltage	V_{DC}	$I_R=0.05\text{ mA}$, $T_j=25\text{ }^{\circ}\text{C}$	1200	-	-	V
Diode forward voltage	V_F	$I_F=7.5\text{ A}$, $T_j=25\text{ }^{\circ}\text{C}$	-	1,65	1,8	
		$I_F=7.5\text{ A}$, $T_j=150\text{ }^{\circ}\text{C}$	-	2,55	-	
Reverse current	I_R	$V_R=1200\text{ V}$, $T_j=25\text{ }^{\circ}\text{C}$	-	8	180	μA
		$V_R=1200\text{ V}$, $T_j=150\text{ }^{\circ}\text{C}$	-	30	1000	

AC characteristics

Total capacitive charge	Q_c	$V_R=400\text{ V}$, $I_F \leq I_{F,max}$, $di_F/dt=200\text{ A}/\mu\text{s}$, $T_j=150\text{ }^{\circ}\text{C}$	-	27	-	nC
Switching time ²⁾	t_c		-	-	<10	ns
Total capacitance	C	$V_R=1\text{ V}$, $f=1\text{ MHz}$	-	380	-	pF
		$V_R=300\text{ V}$, $f=1\text{ MHz}$	-	30	-	
		$V_R=600\text{ V}$, $f=1\text{ MHz}$	-	27	-	

¹⁾ J-STD20 and JESD22

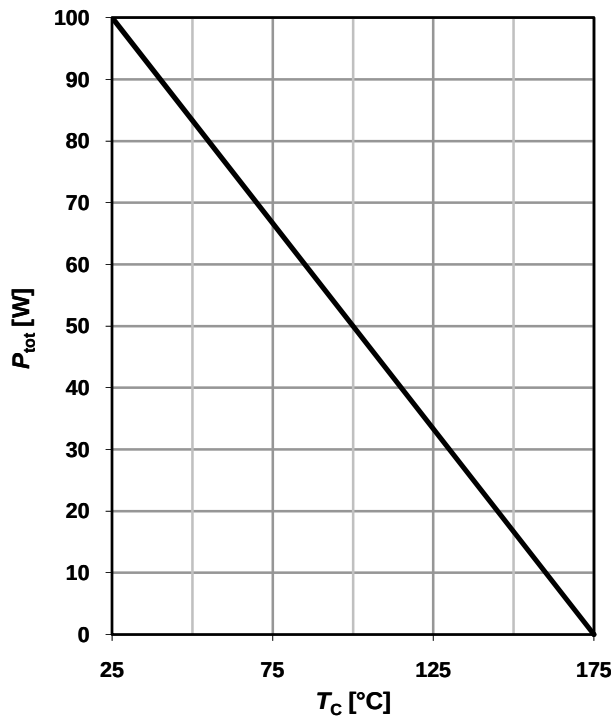
²⁾ t_c is the time constant for the capacitive displacement current waveform (independent from T_j , I_{LOAD} and di/dt), different from t_{rr} which is dependent on T_j , I_{LOAD} and di/dt . No reverse recovery time constant t_{rr} due to absence of minority carrier injection

³⁾ Under worst case Z_{th} conditions.

⁴⁾ Only capacitive charge occurring, guaranteed by design

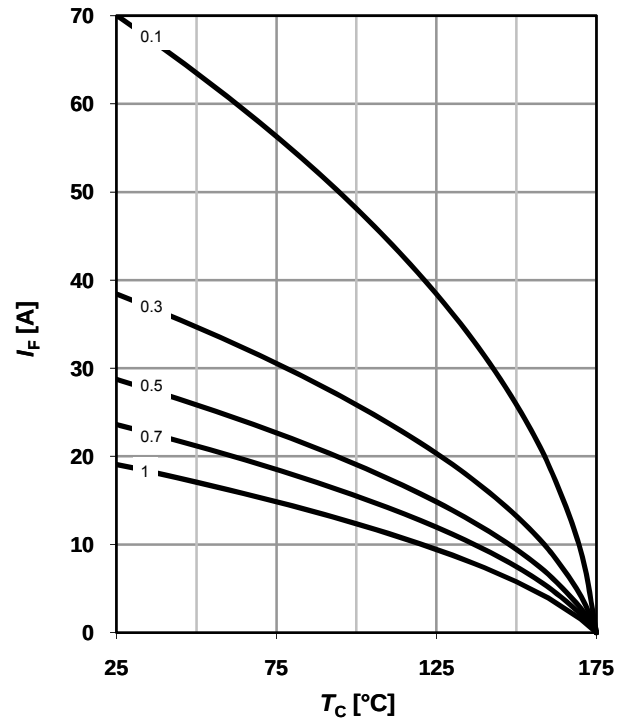
1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



2 Diode forward current

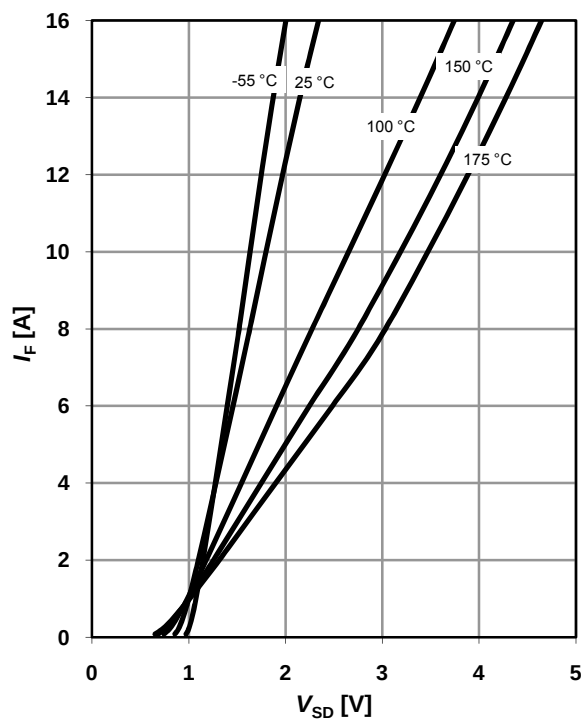
$$I_F = f(T_C)^3; T_j \leq 175 \text{ °C}; \text{ parameter: } D = t_p/T$$



3 Typ. forward characteristic

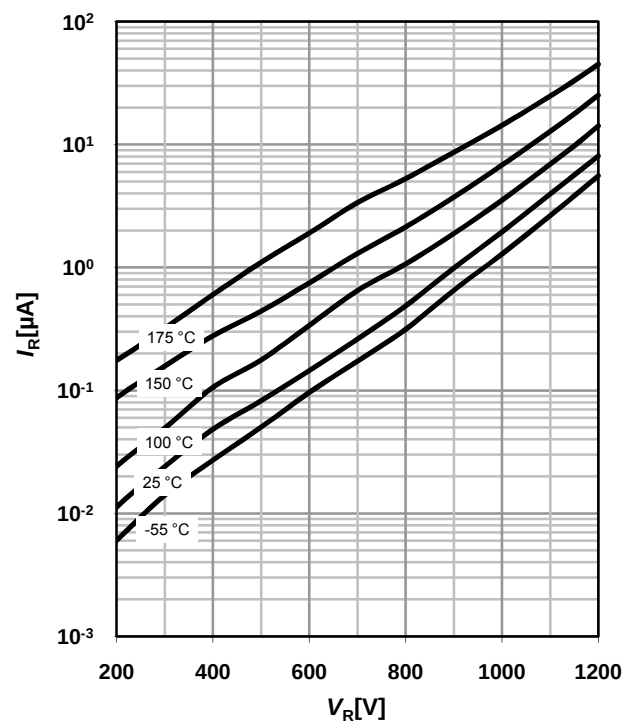
$$I_F = f(V_F); t_p = 400 \text{ } \mu\text{s}$$

parameter: T_j



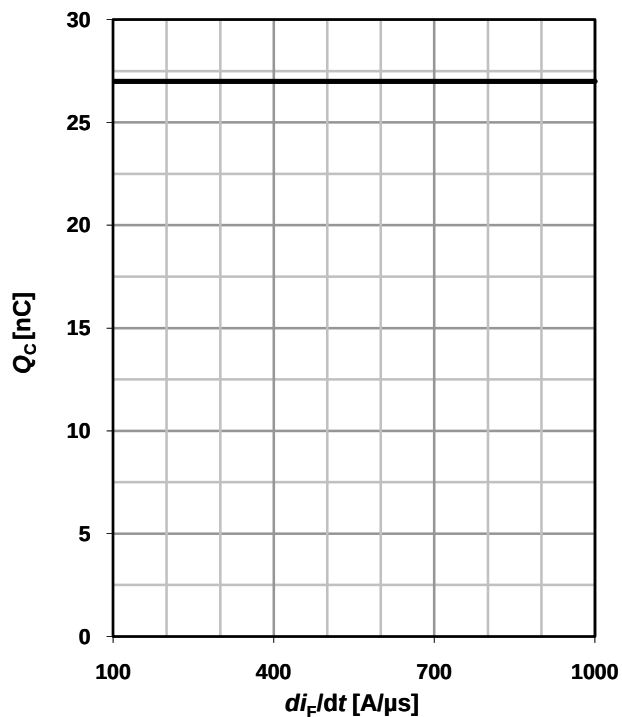
4 Typ. Reverse current vs. reverse voltage

$$E_C = f(V_R)$$



5 Typ. capacitance charge vs. current slope

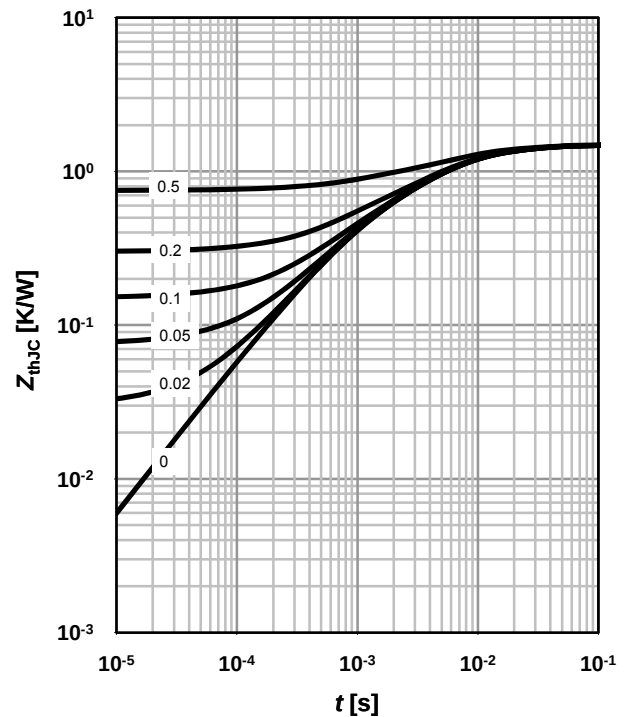
$$Q_C = f(di_F/dt)^{0.4}; T_j = 150^\circ\text{C}; I_F \leq I_{F,\max}$$



6 Transient thermal impedance

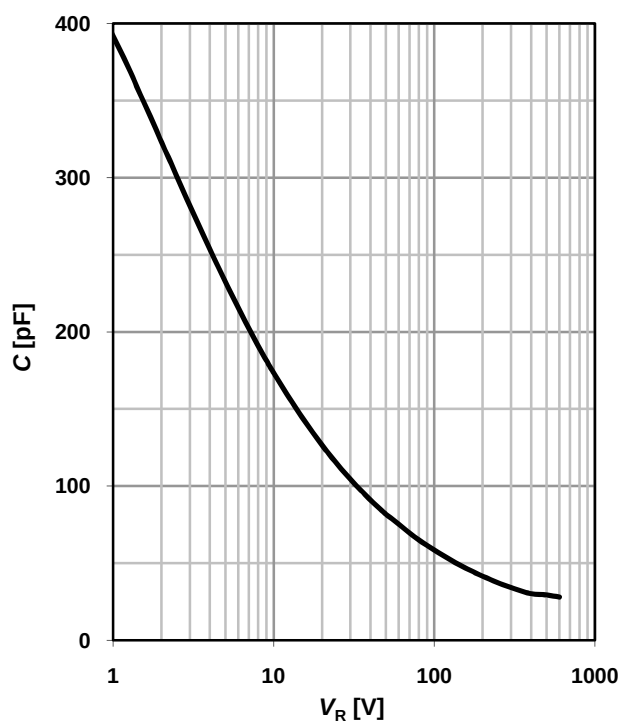
$$Z_{thJC} = f(t_p)$$

$$\text{parameter: } D = t_p/T$$



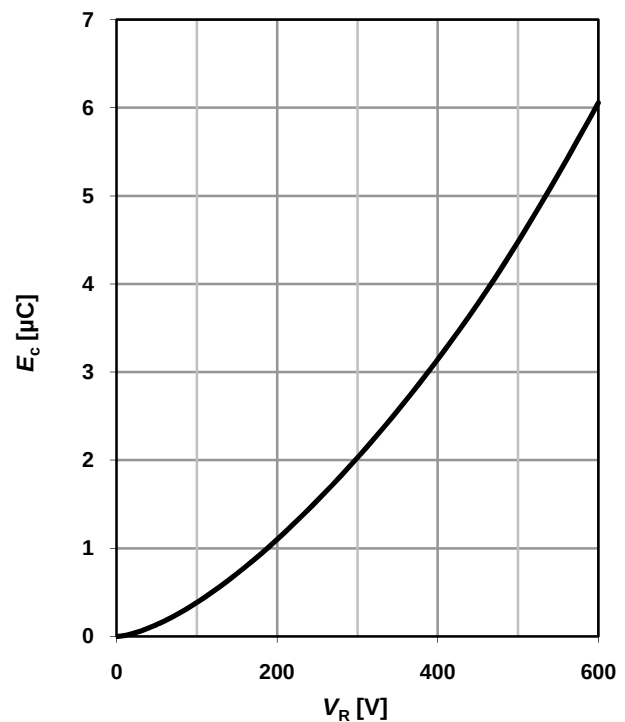
7 Typ. capacitance vs. reverse voltage

$$C = f(V_R); T_C = 25^\circ\text{C}, f = 1\text{ MHz}$$

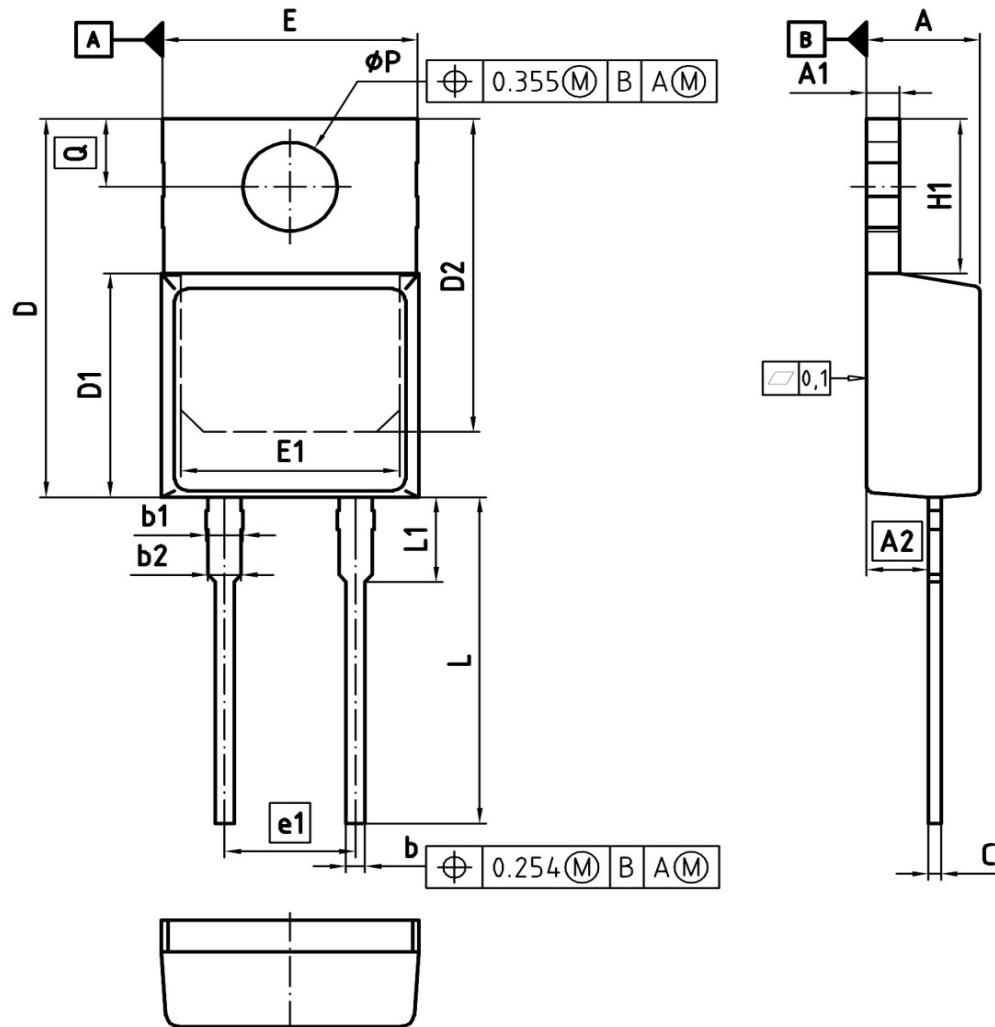


8 Typ. C stored energy

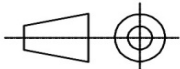
$$E_C = f(V_R)$$



PG-TO220-2: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.50	0.169	0.177
A1	1.17	1.37	0.046	0.054
A2	2.30	2.50	0.091	0.098
b	0.65	0.85	0.026	0.033
b1	1.19	1.69	0.047	0.066
b2	1.19	1.39	0.047	0.055
c	0.40	0.60	0.016	0.024
D	15.35	15.95	0.604	0.628
D1	9.05	9.45	0.356	0.372
D2	12.30	13.05	0.484	0.514
E	9.80	10.20	0.386	0.402
E1	7.25	8.60	0.285	0.339
e1	5.08		0.200	
N	2		2	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	3.30	3.70	0.130	0.146
ϕP	3.55	3.70	0.140	0.146
Q	2.60	3.00	0.102	0.118

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